Vincent LaBella

List of Publications by Year
in descending order

29 papers	495 citations	759233 12 h-index	677142 22 g-index
30 all docs	30 docs citations	30 times ranked	503 citing authors

#	Article	IF	Citations
1	Determination of the energetic resolution of Schottky barrier visualization via interface band structure and parallel momentum conservation. AIP Advances, 2021, 11, .	1.3	1
2	Efficient circuit design for low power energy harvesting. AIP Advances, 2020, 10, .	1.3	6
3	Visualizing metal/HfO2/SiO2/Si(001) interface electrostatic barrier heights with ballistic hole emission microscopy. Journal of Applied Physics, 2019, 126, 195302.	2.5	1
4	Nanoscale Schottky barrier visualization utilizing computational modeling and ballistic electron emission microscopy. Journal of Applied Physics, 2018, 123, .	2.5	3
5	Fermi Level Manipulation through Native Doping in the Topological Insulator Bi₂Se₃. ACS Nano, 2018, 12, 6310-6318.	14.6	37
6	Detection of silicide formation in nanoscale visualization of interface electrostatics. Applied Physics Letters, 2017, 110, 141606.	3.3	6
7	Nanoscale Schottky barrier mapping of thermally evaporated and sputter deposited W/Si(001) diodes using ballistic electron emission microscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	6
8	Relating spatially resolved maps of the Schottky barrier height to metal/semiconductor interface composition. Journal of Applied Physics, 2016, 119, .	2.5	7
9	Pulsed-N2 assisted growth of 5-20 nm thick Î²-W films. AIP Advances, 2015, 5, .	1.3	4
10	Time dependent changes in Schottky barrier mapping of the W/Si(001) interface utilizing ballistic electron emission microscopy. Journal of Applied Physics, 2015, 117, .	2.5	12
11	Synthesis and properties of ferromagnetic nanostructures embedded within a high-quality crystalline silicon matrix via ion implantation and nanocavity assisted gettering processes. Journal of Applied Physics, 2014, 116, 054306.	2.5	3
12	Nanoscale mapping of the W/Si(001) Schottky barrier. Journal of Applied Physics, 2014, 116, 023705.	2.5	9
13	Schottky barrier height measurements of Cu/Si(001), Ag/Si(001), and Au/Si(001) interfaces utilizing ballistic electron emission microscopy and ballistic hole emission microscopy. AIP Advances, 2013, 3, .	1.3	31
14	Signatures of the semiconductor crystallographic orientation on the charge transport across non-epitaxial diodes. Applied Physics Letters, 2012, 100, .	3.3	8
15	Hot-electron transport studies of the Ag/Si(001) interface using ballistic electron emission microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2010, 28, 643-646.	2.1	10
16	Measurement of the hot electron attenuation length of copper. Applied Physics Letters, 2010, 96, .	3.3	18
17	Combined molecular beam epitaxy low temperature scanning tunneling microscopy system: Enabling atomic scale characterization of semiconductor surfaces and interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1684.	1.6	27
18	Magnetic and Structural Properties of Mn-implanted Si. Materials Research Society Symposia Proceedings, 2004, 853, 114.	0.1	1

#	Article	IF	Citations
19	Simultaneous surface topography and spin-injection probability. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 67.	1.6	0
20	Enhancing the Studentâ€Instructor Interaction Frequency. Physics Teacher, 2002, 40, 535-541.	0.3	43
21	Mapping the Spin-Injection Probability on the Atomic Scale. Journal of Superconductivity and Novel Magnetism, 2002, 15, 37-42.	0.5	1
22	A UNION OF THE REAL-SPACE AND RECIPROCAL-SPACE VIEW OF THE GaAs(001) SURFACE. International Journal of Modern Physics B, 2001, 15, 2301-2333.	2.0	8
23	Spatially Resolved Spin-Injection Probability for Gallium Arsenide. Science, 2001, 292, 1518-1521.	12.6	94
24	Microscopic structure of spontaneously formed islands on the GaAs(001)-(2Ã—4) reconstructed surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1640.	1.6	6
25	Enabling electron diffraction as a tool for determining substrate temperature and surface morphology. Applied Physics Letters, 2001, 79, 3065-3067.	3.3	24
26	Reflection high-energy electron diffraction and scanning tunneling microscopy study of InP(001) surface reconstructions. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1492-1496.	2.1	27
27	Monte Carlo derived diffusion parameters for Ga on the GaAs(001)- (2Ã—4) surface: A molecular beam epitaxyâ€“scanning tunneling microscopy study. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1526-1531.	2.1	40
28	Role of As[sub 4] in Ga diffusion on the GaAs(001)-(2Ã—4) surface: A molecular beam epitaxy-scanning tunneling microscopy study. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1778.	1.6	22
29	Measurement of hot-electron scattering processes at Au/Si(100) Schottky interfaces by temperature-dependent ballistic-electron-emission microscopy. Physical Review B, 1996, 53, 3952-3959.	3.2	40